## Notice of References Cited Application/Control No. 10/748,617 Examiner Allan Olsen Applicant(s)/Patent Under Reexamination METZ ET AL. Page 1 of 1

## U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	Α	US-6,773,616 B1	08-2004	Chen et al.	216/41
*	В	US-2004/0144970 A1	07-2004	Wang et al.	257/017
*	С	US-2002/0130311 A1	09-2002	Lieber et al.	257/1
*	D	US-2004/0113139 A1	06-2004	DeHon et al.	257/009
*	E	US-2004/0026684 A1	02-2004	Empedocles, Stephen	257/14
	F	US-			
	G	US-			
	Н	US-			
	1	US-			
	J	US-			
	к	US-			
	L	US-			
	М	US-			

## FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	Ν					
	0			•		
	Р					
*	α					
	R					
	S					
	Т					

## **NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)				
	U	Yiying Wu et al., Block-by-Block Growth of Single Crystalline Si/SiGe Superlattice Nanowires, Nano Letters, February 2002, Vol. 2, No. 2, pp. 83-86.				
	<b>V</b>	M. T. Bjork et al., One-dimensional Steeplechase for Electrons Realized, Nano Letters, February 2002, Vol. 2, No. 2, pp. 87-8				
	w	Gudiksen et al., Growth of Nanowire Superlattice Structures for Nanoscale Photonics and Electronics, Nature 2001, Vol. 41 617-620.				
	x					

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.